

SavantIC Semiconductor

Product Specification

Silicon NPN Power Transistors

BD707 BD709 BD711

DESCRIPTION

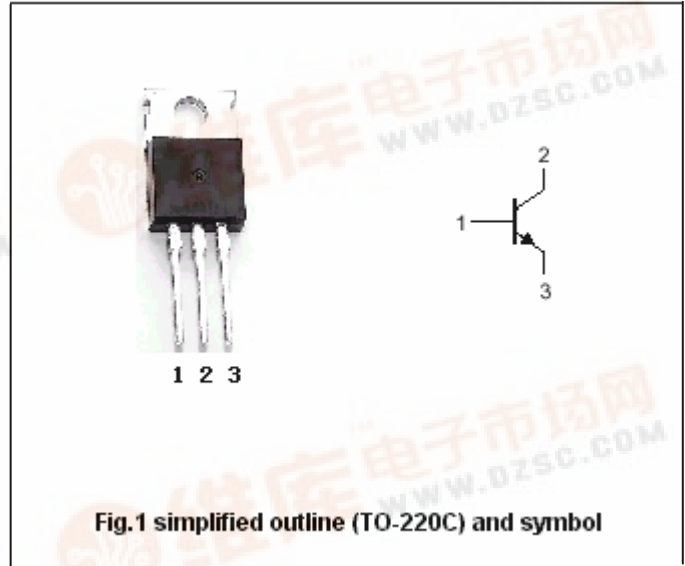
- With TO-220C package
- The BD707 and BD711are respectively complement to type BD708 and BD712

APPLICATIONS

- Intended for use in power linear and switching applications.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	BD707	60	V
		BD709	80	
		BD711	100	
V _{CEO}	Collector-emitter voltage	BD707	60	V
		BD709	80	
		BD711	100	
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current-DC		12	A
I _{CM}	Collector current-Pulse		18	A
I _B	Base current		5	A
P _T	Total dissipation	T _C =25□	75	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-65~150	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction to case	1.67	□/W

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	BD707	I _C =0.1A, I _B =0	60		V		
		BD709		80				
		BD711		100				
V _{CEsat}	Collector-emitter saturation voltage	I _C =4A, I _B =0.4A			1.0	V		
V _{BE}	Base-emitter voltage	I _C =4A, V _{CE} =4V			1.5	V		
I _{CBO}	Collector cut-off current	BD707	V _{CB} =60V, I _E =0 T _C =150 °C			0.1	mA	
		BD709		V _{CB} =80V, I _E =0 T _C =150 °C				0.1
		BD711		V _{CB} =100V, I _E =0 T _C =150 °C				0.1
I _{CEO}	Collector cut-off current	BD707	V _{CE} =30V, I _B =0			0.1	mA	
		BD709		V _{CE} =40V, I _B =0				
		BD711		V _{CE} =50V, I _B =0				
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1.0	mA		
h _{FE-1}	DC current gain	I _C =0.5A; V _{CE} =2V	40	120	400			
h _{FE-2}	DC current gain only for BD707/709	I _C =2A; V _{CE} =2V	30					
h _{FE-3}	DC current gain	I _C =4A; V _{CE} =2V	15		150			
h _{FE-4}	DC current gain	BD707	I _C =10A; V _{CE} =4V	5	10			
		BD709		8				
		BD711		8				
f _T	Transition frequency	I _C =0.3A; V _{CE} =3V;	3			MHz		

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PACKAGE OUTLINE

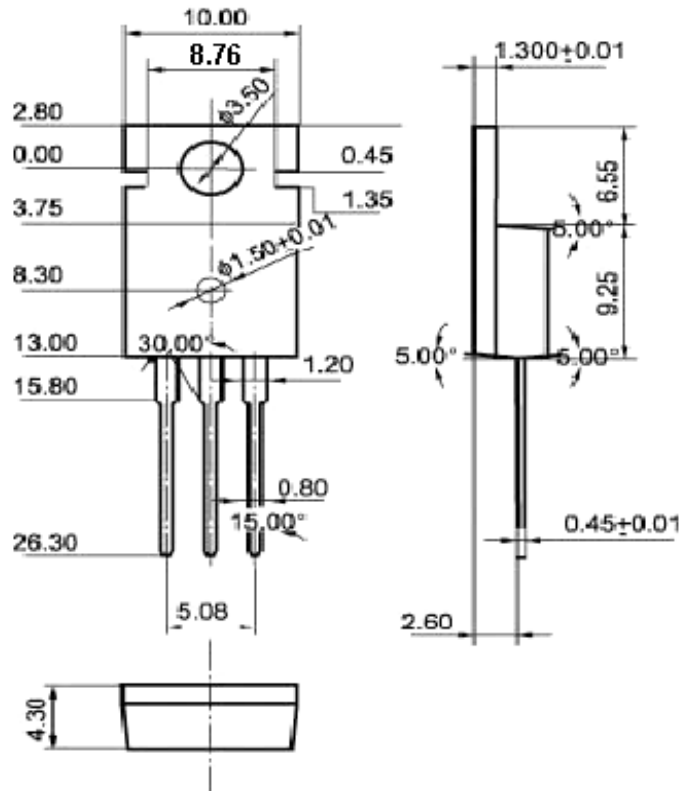


Fig.2 Outline dimensions